

2N6298 & 2N6299



PNP Darlington Power Silicon Transistor

Rev. V4

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/540
- TO-66 (TO-213AA) Package
- Ideal for High Gain Amplifier and Medium Speed Switching Applications



Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_C = -100\text{ mA dc}$, 2N6298 $I_C = -100\text{ mA dc}$, 2N6299	$V_{(BR)CEO}$	V dc	-60 -80	—
Collector - Emitter Cutoff Current	$V_{CE} = -30\text{ V dc}$, 2N6298 $V_{CE} = -40\text{ V dc}$, 2N6299	I_{CEO}	mA dc	—	-0.5 -0.5
Collector - Emitter Cutoff Current	$V_{CE} = -60\text{ V dc}$, $V_{BE} = +1.5\text{ V dc}$, 2N6298 $V_{CE} = -80\text{ V dc}$, $V_{BE} = +1.5\text{ V dc}$, 2N6299	I_{CEX1}	$\mu\text{A dc}$	—	-10 -10
Emitter - Base Cutoff Current	$V_{EB} = -5\text{ V dc}$	I_{EBO}	mA dc	—	-2.0
Forward - Current Transfer Ratio	$V_{CE} = -3\text{ V dc}$, $I_C = -1\text{ A dc}$ $V_{CE} = -3\text{ V dc}$, $I_C = -4\text{ A dc}$ $V_{CE} = -3\text{ V dc}$, $I_C = -8\text{ A dc}$	h_{FE}	-	500 750 100	18,000
Collector - Emitter Saturation Voltage	$I_C = -4\text{ A dc}$, $I_B = -16\text{ mA dc}$ $I_C = -8\text{ A dc}$, $I_B = -80\text{ mA dc}$	$V_{CE(sat)1}$ $V_{CE(sat)2}$	V dc	—	-2.0 -2.0
Base - Emitter Saturation Voltage	$I_C = -8\text{ A dc}$, $I_B = -80\text{ A dc}$	$V_{BE(sat)}$	V dc	—	-4.0
Base - Emitter Voltage	$V_{CE} = -3\text{ V dc}$, $I_C = -4\text{ A dc}$	$V_{BE(on)}$	V dc	—	-2.8
Collector - Emitter Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CE} = -60\text{ V dc}$, $V_{BE} = +1.5\text{ V dc}$, 2N6298 $V_{CE} = -80\text{ V dc}$, $V_{BE} = +1.5\text{ V dc}$, 2N6299	I_{CEX2}	mA dc	—	-5.0 -5.0
Forward - Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $V_{CE} = -3\text{ V dc}$, $I_C = -4\text{ A dc}$	h_{FE4}	-	200	
Dynamic Characteristics					
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	$V_{CE} = -3\text{ V dc}$, $I_C = -3\text{ A dc}$, $f = 1.0\text{ MHz}$	$ h_{fe} $	-	25	350
Small-Signal Short-Circuit Forward - Current Transfer Ratio	$V_{CE} = -3\text{ V dc}$, $I_C = -3\text{ A dc}$, $f = 1.0\text{ kHz}$	h_{fe}	-	300	—
Open Circuit Output Capacitance	$V_{CB} = -10\text{ V dc}$, $I_E = 0$, $100\text{ kHz} \leq f \leq 1\text{ MHz}$	C_{obo}	pF	—	200
Switching Characteristics					
Turn-On Time	$V_{CC} = -30\text{ V dc}$; $I_C = -4\text{ A dc}$; $I_{B1} = -16\text{ mA dc}$	t_{on}	μs	—	2.0
Turn-Off Time	$V_{CC} = -30\text{ Vdc}$; $I_C = -4\text{ A dc}$; $I_{B1} = -16\text{ mA dc}$	t_{off}	μs	—	8.0

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Absolute Maximum Ratings ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N6298 2N6299	V_{CEO}	-60 V dc -80 V dc
Collector - Base Voltage 2N6298 2N6299	V_{CBO}	-60 V dc -80 V dc
Emitter - Base Voltage	V_{EBO}	-5 V dc
Base Current	I_B	-120 mA dc
Collector Current	I_C	-8 A dc
Total Power Dissipation ⁽¹⁾ @ $T_C = +25^\circ\text{C}$ @ $T_C = +100^\circ\text{C}$	P_T	64 W 32 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to $+175^\circ\text{C}$

(1) Derate linearly at 0.428 W/ $^\circ\text{C}$ above $T_C > +25^\circ\text{C}$.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.33°C/W

Safe Operating Area

DC Tests:	$T_C = +25^\circ\text{C} + 10^\circ\text{C}$, 1 Cycle, $t = 1.0$ s
Test 1:	$V_{CE} = -8.0$ V dc, $I_C = -8.0$ A dc
Test 2:	$V_{CE} = -20$ V dc, $I_C = -2.0$ A dc
Test 3:	$V_{CE} = -60$ V dc, $I_C = -100$ mA dc, 2N6298
	$V_{CE} = -80$ V dc, $I_C = -100$ mA dc, 2N6299

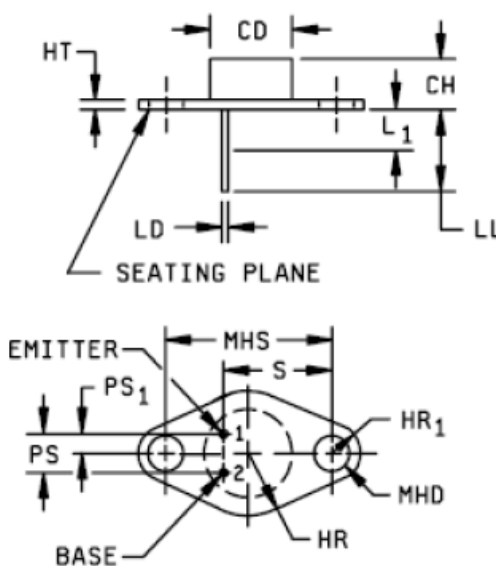
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Outline Drawing (TO-66)

Dimensions					
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD		.620		15.76	
CH	.250	.340	6.35	8.64	
HR		.350		8.89	
HT	.050	.075	1.27	1.91	
HR ₁	.115	.145	2.92	3.68	4
LD	.028	.034	.71	.86	4, 6
LL	.360	.500	9.14	12.70	
L ₁		.050		1.27	6
MHD	.142	.152	3.61	3.86	4
MHS	.958	.962	24.33	24.43	
PS	.190	.210	4.83	5.33	3
PS ₁	.093	.107	2.36	2.73	3
S	.570	.590	14.48	14.99	
Notes	1, 2, 5, 7				



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. These dimensions should be measured at points .050 inch (1.27 mm) +.005 inch (0.13 mm) -.000 inch (0.00 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
4. Two places.
5. The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
6. Lead diameter shall not exceed twice LD within L₁.
7. Lead number 1 is the emitter, lead 2 is the base, case is the collector.
8. In accordance with ASME Y14.5M, diameters are equivalent to $\varnothing$ x symbology.

FIGURE 1. Physical dimensions (similar to TO-66).

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